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## CORRECTION

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with a high mobility level of 2.0 cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>

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Correction: An ambipolar organic field-effect

transistor based on an AIE-active single crystal

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Correction for 'An ambipolar organic field-effect transistor based on an AIE-active single crystal with a high mobility level of  $2.0 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$  by Jian Deng et al., Chem. Commun., 2016, DOI: 10.1039/c5cc09702a.

The authors regret that the CSD refcode (VIGNIK) was not provided for the crystal structure (CCDC 860278) discussed in the original manuscript, and the CCDC number itself was presented instead. The following refcode link provides access to the details for CCDC 860278, which was originally reported in *Journal of Physical Chemistry Part C: Nanomaterials and Interfaces*, 2012, 116, 15146.

www.ccdc.cam.ac.uk/services/structures?pid=csd:VIGNIK&sid=CCDCManual

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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